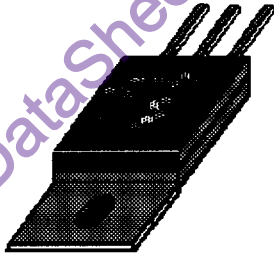


8.0 Amp SILICON CONTROLLED PLASTIC RECTIFIERS

10/93

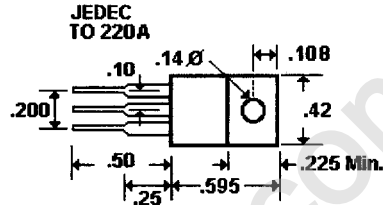
Description

CR800-2....- 8 Series



Mechanical Dimensions

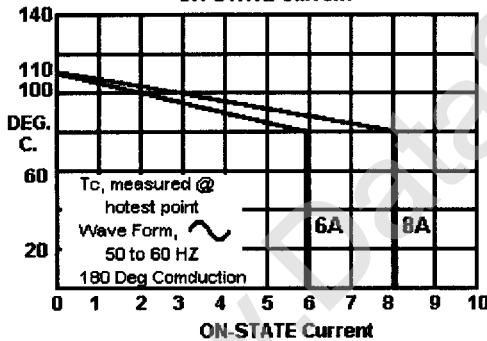
CR800-2....- 8 Series



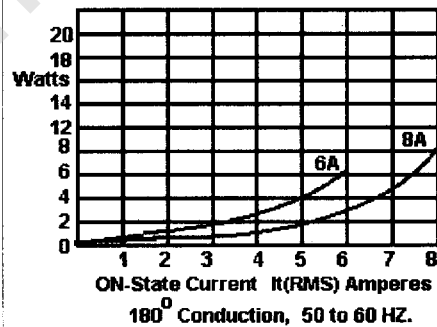
Features

- O IC Compatible (TTL & MOS)
- O Non-Sensitive gate Trigger
- O Voltage Ratings From 50V to 600V
- O Void Free Passivated Glass Passivated Chips

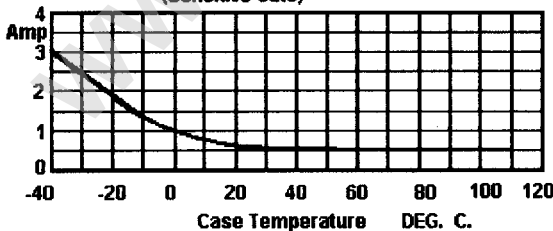
Maximum Allowable case Temperature vs. ON-STATE Current



Maximum Conduction Power Dissipation vs. ON-State Current

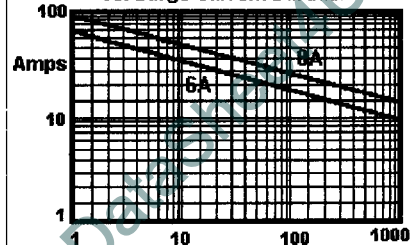


Typical Gate Current vs. Case Temperature (Sensitive Gate)



Surge current duration, full cycle @ 60HZ
Current wave form 60 HZ, Sinesoidal
Resistive load, $I_t(rms)$ = Amps @ 50 Deg. C.

Peak Surge On State Current vs. Surge Current Duration



Gate control maybe lost during and after surge. Gate control will be regained after T_j returns to steady state value

8.0 Amp SILICON CONTROLLED PLASTIC RECTIFIERS

Electrical Characteristics @ 25 Deg. C.

Maximum Ratings		Voltage	CR800-2.....- 8 Series
Repetitive Peak Offstate Voltage...VDRM		50	CR800-2
Maximum Repetitive Peak Reverse Voltage...VRRM		100	CR800-3
Tc = 125 C.		200	CR800-4
Tstg.....-40 to 150 deg. C.	Toper.....-40 to 110 deg. C.	400	CR800-6
		600	CR800-8
RMS On State Current It(rms)			8
Tc = 50 C., Conduction Angle 180 Deg.			
Peak Surge Non-Repetitive On State Current I _{tsm}			40
One cycle at 50 or 60 HZ			
Peak Gate Trigger Current I _{gtm}			1
3 uS Max			
Peak Gate Power Dissipation P _{gm}			.5
I _{gt} = I _{gtm}			
Average Gate Power Dissipation P _{g(av)}			.2
Peak Off State Current I _{dsm} & I _{rrm}	TC = 25 Deg. C.		10
RG-K=1K ohms, V _{dsm} & V _{rrm} = Max.	TC = 125 Deg. C.		200
Maximum On-State Voltage (Peak) V _{tm}			2.2
I _t = Rated Amps, TC = 25 C.			
DC Holding Current I _{ho}			5.0
Gate Open & TC = 25 C.			
Critical Rate of Rise of OFF State Voltage	Critical Dv/Dt		8.0
Gate Open & TC = 110 C.			
DC Gate Trigger Current for Anode I _{gt}			200
Voltage = 7VDC, R _i = 100 ohms, TC = 25 C.			
DC Gate Trigger Voltage for Anode V _{gt}			1.0
Voltage = 7VDC, R _i = 100 ohms, TC = 25 C.			
Gate Controlled Turn On Time (T _d + T _r) T _{gt}			2.2
I _{ct} = 10 mA, TC = 25 C.			
Thermal Resistance , Junction to case			2.2